

L Number	Hits	Search Text	DB	Time stamp
-	1	("6154328").PN.	USPAT; US-PGPUB	2003/07/14 13:00
-	7	Magnetoelectric near3 sensing	USPAT; US-PGPUB	2003/07/14 13:07
-	606	Magnetoresistive near3 sensing	USPAT; US-PGPUB	2003/07/14 13:09
-	5	microfine near2 (wire wiring)	USPAT; US-PGPUB	2003/07/14 13:08
-	468735	resin	USPAT; US-PGPUB	2003/07/14 13:08
-	0	(Magnetoresistive near3 sensing) and (microfine near2 (wire wiring))	USPAT; US-PGPUB	2003/07/14 13:08
-	22	(Magnetoresistive near3 sensing) and resin	USPAT; US-PGPUB	2003/07/14 13:08
-	110	stack\$3 and Magnetoresistive near3 sensing	USPAT; US-PGPUB	2003/07/14 13:09
-	468735	resin	USPAT; US-PGPUB	2003/07/14 13:09
-	3	(stack\$3 and Magnetoresistive near3 sensing) and resin	USPAT; US-PGPUB	2003/07/14 14:16
-	1	("5393351").PN.	USPAT; US-PGPUB	2003/07/14 14:17
-	269	(73/104.26).CCLS.	USPAT; US-PGPUB	2003/07/14 14:25
-	564048	resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane	USPAT; US-PGPUB	2003/07/14 14:48
-	52	((73/204.26).CCLS.) and (resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane)	USPAT; US-PGPUB	2003/07/14 14:47
-	3	Magnetoresistive near3 (resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane)	USPAT; US-PGPUB	2003/07/14 14:51
-	5	Magnetoresistive near3 (resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane)	EPO; JPO; DEPWENT	2003/07/14 15:09
-	61	Magnetoresistive and (resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane)	EPO; JPO; DEPWENT	2003/07/14 14:55
-	56	(Magnetoresistive and (resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane)) not (Magnetoresistive near3 (resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane))	EPO; JPO; DEPWENT	2003/07/14 15:07
-	2	microfine adj wir\$3	EPO; JPO; DEPWENT	2003/07/14 15:07
-	1	microfine adj wir\$3	US-PGPUB	2003/07/14 15:08
-	152	fusing adj temperature	US-PGPUB	2003/07/14 15:08
-	1150	curing adj temperature	US-PGPUB	2003/07/14 15:08
-	3	(fusing adj temperature) and (curing adj temperature)	US-PGPUB	2003/07/14 15:08
-	3	Magnetoresistive near3 (resin silicone siloxane polysiloxane polyorganosiloxane polydiorganosiloxane)	USEPAT; US-PGPUB	2003/07/14 15:44
-	203284	control adj circuit	USEPAT; US-PGPUB	2003/07/14 16:30
-	72	(Magnetoresistive near3 sensing) and (control adj circuit)	USEPAT; US-PGPUB	2003/07/14 15:45
-	1	2000WO-JP03077.ap,prai.	EPO; JPO; DEPWENT	2003/07/14 16:31
-	5468	FUKAMI-T\$.in. KAWANO-Y\$.in. TAGUCHI-M\$.in. YASUDA-N\$.in.	EPO; JPO; DEPWENT	2003/07/14 16:32
-	795181	sensor	EPO; JPO; DEPWENT	2003/07/14 16:32
-	268	(FUKAMI-T\$.in. KAWANO-Y\$.in. TAGUCHI-M\$.in. YASUDA-N\$.in.) and sensor	EPO; JPO; DEPWENT	2003/07/14 16:34

Search History 7/25/03 11:07:04 AM Page 1

-	1187698	resin	EPO; JPO;	2003/07/14
-			DEPWENT	16:34
-	13	((FUKAMI-T\$.in. KAWANO-Y\$.in. TAGUCHI-M\$.in. YASUDA-N\$.in.) and sensor)	EPO; JPO;	2003/07/14
-		and resin	DEPWENT	16:37
-	5443	magnetoresistive	EPO; JPO;	2003/07/14
-			DEPWENT	16:37
-	2	((FUKAMI-T\$.in. KAWANO-Y\$.in. TAGUCHI-M\$.in. YASUDA-N\$.in.) and sensor)	EPO; JPO;	2003/07/14
-		and magnetoresistive	DEPWENT	16:39
-	1	EP-1058324-\$.did.	EPO	2003/07/14
-				16:45
-	97596	air adj flow	EPO; JPO;	2003/07/14
-			DEPWENT	16:46
-	17	(FUKAMI-T\$.in. KAWANO-Y\$.in. TAGUCHI-M\$.in. YASUDA-N\$.in.) and (air adj flow)	EPO; JPO;	2003/07/14
-			DEPWENT	16:46

L Number	Hits	Search Text	DB	Time stamp
-	1	2000WO-jp03077.ap.prai.	EPO; JPO;	2002/12/16
-	5260	FUKAMI-T\$.in. KAWANO-Y\$.in.	DEFWENT	11:42
-	763373	TAGUCHI-M\$.in. YASUDA-N\$.in.	EPO; JPO;	2002/12/16
-		sensor	DEFWENT	09:18
-	255	(FUKAMI-T\$.in. KAWANO-Y\$.in.	EPO; JPO;	2002/12/16
-	7158	TAGUCHI-M\$.in. YASUDA-N\$.in.) and sensor	DEFWENT	09:18
-		photocur\$	EPO; JPO;	2002/12/16
-			DEFWENT	09:18
-	0	((FUKAMI-T\$.in. KAWANO-Y\$.in.	EPO; JPO;	2002/12/16
-	109071	TAGUCHI-M\$.in. YASUDA-N\$.in.) and sensor) and photocur\$	DEFWENT	09:19
-		silicone	EPO; JPO;	2002/12/16
-	5	((FUKAMI-T\$.in. KAWANO-Y\$.in.	DEFWENT	09:19
-		TAGUCHI-M\$.in. YASUDA-N\$.in.) and sensor; and silicone	EPO; JPO;	2002/12/16
-	2	Gb-2322452-\$.did.	DEFWENT	09:31
-	2	JP-10054843-\$.did.	EPO; JPO;	2002/12/16
-	0	JP-100013616-\$.did.	DEFWENT	09:32
-	2	JP-10013616-\$.did.	EPO; JPO;	2002/12/16
-	2	JP-60062279-\$.did.	DEFWENT	09:33
-	2	JP-61080039-\$.did.	EPO; JPO;	2002/12/16
-	1	JP-62178359-\$.did.	DEFWENT	09:33
-	2	JP-09078755-\$.did.	EPO; JPO;	2002/12/16
-	750	428/447	DEFWENT	09:34
-	3567	(428/447).CCLS.	EPO; JPO;	2002/12/16
-	379253	sensor	DEFWENT	10:58
-	71	((428/447).CCLS.) and sensor	EPO; JPO;	2002/12/16
-	70668	((magnetoresistance (air adj flow)	DEFWENT	10:59
-	8	acceleration pressure (yaw adj rate)	USPAT;	2002/12/16
-		image) near2 (sensor))	US-PGPUB	11:29
-		((((428/447).CCLS.) and sensor) and	USPAT;	2002/12/16
-		((magnetoresistance (air adj flow)	US-PGPUB	10:59
-		acceleration pressure (yaw adj rate)	USPAT;	2002/12/16
-		image) near2 (sensor))	US-PGPUB	11:17
-	252849	molecular adj weight	USPAT;	2002/12/16
-	32	((((428/447).CCLS.) and sensor) and	US-PGPUB	11:18
-	0	(molecular adj weight)	USPAT;	2002/12/16
-	330	magnetoresistance near2 sensor	US-PGPUB	11:10
-	0	((((428/447).CCLS.) and sensor) and	USPAT;	2002/12/16
-		(magnetoresistance near2 sensor)	US-PGPUB	11:17
-	0	(molecular adj weight) and	USPAT;	2002/12/16
-		((((428/447).CCLS.) and sensor) and	US-PGPUB	11:18
-		(magnetoresistance near2 sensor))	USPAT;	2002/12/16
-	70988	((magnetoresistance (air adj flow)	US-PGPUB	11:18
-		acceleration pressure (yaw adj rate)	USPAT;	2002/12/16
-		image) near2 (sensor))	US-PGPUB	11:19
-	0	(magnetoresistance near2 sensor)	USPAT;	2002/12/16
-		wire near2 substract	US-PGPUB	11:19

-	5562	wire near2 substrate	USPAT;	2002/12/16
-			US-PGPUB	11:20
-	10	wire near4 (polymer adj substrate)	USPAT;	2002/12/16
-			US-PGPUB	11:21
-	1580	(molecular adj weight) and	USPAT;	2002/12/16
-		((428/447).CCLS.)	US-PGPUB	11:25
-	32	sensor and ((molecular adj weight) and	USPAT;	2002/12/16
-		((428/447).CCLS.))	US-PGPUB	11:25
-	2	jp-10319597-\$.did.	EPO; JPO;	2002/12/16
-			DERWENT	11:43